

**=> IFW: Scan as Doc Code: SRNT <=
 Doc Date:**

TC 3700 Inventor Search Program

See attached inventor searches for applications and/or patents to help resolve questions of overlapping subject matter. These searches are provided as an initial examination aid: examiners should perform updated or expanded PALM or EAST inventors searches as appropriate.

Serial Number: 10/821798

**1.) See attached printout of inventors listed in
PALM**

**2.) See attached EAST Inventor Search
Printout shows Inventor search terms**

Day : Tuesday
Date: 8/29/2006
Time: 15:27:04

 **PALM INTRANET**

Inventor Information for 10/821798

Inventor Name	City	State/Country
FRANOSCH, MARTIN	MUNCHEN	GERMANY
MECKES, ANDREAS	MUNCHEN	GERMANY
OPPERMANN, KLAUS-GUNTER	HOLZKIRCHEN	GERMANY

[Appln Info](#)[Contents](#)[Petition Info](#)[Atty/Agent Info](#)[Continuity/Reexam](#)[Foreign Data](#)[Invento](#)Search Another: Application# or Patent# PCT / / or PG PUBS # Attorney Docket # Bar Code #

To go back use Back button on your browser toolbar.

Back to [PALM](#) | [ASSIGNMENT](#) | [OASIS](#) | [Home page](#)

US 20060191868 A1	20060831	Concept for the wet-chemical removal of a sacrificial material in a material structure	216/83	438/745	Franosch; Martin et al.
US 20060183325 A1	20060817	Lift-off method	438/670		Franosch; Martin et al.
US 20050148205 A1	20050707	Method for producing a protective cover for a device	438/783		Franosch, Martin et al.
US 20050146022 A1	20050707	Apparatus for housing a micromechanical structure and method for producing the same	257/704		Franosch, Martin et al.
US 20050079686 A1	20050414	Method for producing a cover, method for producing a packaged device	438/458	438/110; 438/118; 438/48; 438/64; 438/68	Aigner, Robert et al.
US 20050048757 A1	20050303	Method for generating a protective cover for a device	438/614		Aigner, Robert et al.
US 20050009316 A1	20050113	Method for producing a protective cover for a device	438/613		Franosch, Martin et al.
US 20050006723 A1	20050113	Bipolar transistor	257/565	257/E21.379; 257/E29.184	Stengl, Reinhard et al.
US 20040201090 A1	20041014	Electronic device with cavity and a method for producing the same	257/686	257/777; 257/E23.039; 257/E23.124; 438/109	Aigner, Robert et al.
US 20040161909 A1	20040819	Electronic component and method for its production	438/460		Meckes, Andreas et al.

US 20040104402 A1	20040603	Configuration and method for making contact with the back surface of a semiconductor substrate	257/181		Birner, Albert et al.
US 20040099881 A1	20040527	Bipolar transistor and method for fabricating it	257/197	257/200; 257/E21.371; 257/E29.193; 438/309; 438/312	Franosch, Martin et al.
US 20040067650 A1	20040408	Method for manufacturing a housing for a chip having a micromechanical structure	438/689		Dache, Frank et al.
US 20030201479 A1	20031030	Method for fabricating trench capacitors and semiconductor device with trench capacitors	257/301	257/309; 438/386; 438/389; 438/398	Birner, Albert et al.
US 20030178700 A1	20030925	Silicon bipolar transistor, circuit arrangement and method for production of a silicon bipolar transistor	257/565	257/E29.044	Franosch, Martin et al.
US 20030117158 A1	20030626	Contact spring configuration for contacting a semiconductor wafer and method for producing a contact spring configuration	324/754	324/757	Goldbach, Matthias et al.
US 20030020139 A1	20030130	Bipolar transistor and method of fabricating a bipolar transistor	257/565	257/E21.379; 257/E29.184	Stengl, Reinhard et al.
US	20021114	Method for	438/309	257/E21.371;	Bock, Josef

20020168829 A1		fabricating a bipolar transistor and method for fabricating an integrated circuit configuration having such a bipolar transistor		257/E21.379	et al.
US 20020126543 A1	20020912	STORAGE CAPACITOR FOR A DRAM	365/200	257/E21.647; 257/E27.085	Reisinger, Hans et al.
US 20020121662 A1	20020905	Method for producing a vertical semiconductor transistor component and vertical semiconductor transistor component	257/329	257/330; 257/E21.404; 257/E21.41; 257/E21.629; 257/E27.06; 257/E29.322; 257/E51.006; 257/E51.04; 438/212; 438/259; 438/270; 438/589	Rosner, Wolfgang et al.
US 20020117715 A1	20020829	Semiconductor component for high reverse voltages in conjunction with a low on resistance and method for fabricating a semiconductor component	257/339	257/202; 257/342; 257/E21.42; 257/E29.013; 257/E29.021; 257/E29.04; 257/E29.066; 257/E29.257; 257/E29.259	Oppermann, Klaus- Gunter et al.
US 20020086455 A1	20020704	Method for the manufacture of micro-mechanical components	438/51	438/48; 438/50	Franosch, Martin et al.
US 20010055858 A1	20011227	Method for making electrical contact with a rear side of a semiconductor substrate during its processing	438/466	438/100	Birner, Albert et al.

US 20010054315 A1	20011227	Micromechanical component protected from environmental influences	73/727		Aigner, Robert et al.
US 20010048139 A1	20011206	Deformation gauge	257/415		Aigner, Robert et al.
US 20010031526 A1	20011018	DRAM memory capacitor, and method for its production	438/238	257/E21.01; 257/E21.272; 438/3	Beitel, Gerhard et al.
US 20010023969 A1	20010927	Integrated circuit and method of manufacturing same	257/402	257/E21.632; 257/E27.064	Lustig, Bernhard et al.
US 20010021538 A1	20010913	Micromechanical component and process for its fabrication	438/22		Aigner, Robert et al.
US 20010020730 A1	20010913	Integrated circuit configuration, method for producing it, and wafer including integrated circuit configurations	257/617	257/629; 257/E21.646; 257/E27.085; 257/E29.004	Stengl, Reinhard et al.
US 20010013773 A1	20010816	Configuration with a plurality of sensor groups and method of determining its intactness	324/158.1		Aigner, Robert et al.
US 20010005032 A1	20010628	Method for producing a filled recess in a material layer, and an integrated circuit configuration produced by the method	257/415	438/53	Aigner, Robert et al.
US 7064360 B2	20060620	Bipolar transistor and method for fabricating it	257/197	257/201; 257/E21.371; 257/E29.193; 438/312	Franosch, Martin et al.

US 7061098 B2	20060613	Electronic component and method for its production	257/704	257/701	Meckes; Andreas et al.
US 7037844 B2	20060502	Method for manufacturing a housing for a chip having a micromechanical structure	438/706	438/106; 438/107; 438/745	D che; Frank et al.
US 6955950 B2	20051018	Method for generating a protective cover for a device	438/125	257/701; 257/704; 438/110	Aigner; Robert et al.
US 6939734 B2	20050906	Method for producing a protective cover for a device	438/53	438/619	Franosch; Martin et al.
US 6909141 B2	20050621	Method for producing a vertical semiconductor transistor component and vertical semiconductor transistor component	257/329	257/327; 257/328; 257/330; 257/331; 257/E21.404; 257/E21.41; 257/E21.629; 257/E27.06; 257/E29.322; 257/E51.006; 257/E51.04; 438/212; 438/259; 438/270; 438/589	Rosner; Wolfgang et al.
US 6903454 B2	20050607	Contact spring configuration for contacting a semiconductor wafer and method for producing a contact spring configuration	257/688	257/727; 324/757	Goldbach; Matthias et al.
US 6878600 B2	20050412	Method for fabricating trench capacitors and	438/386	257/301; 257/309; 438/243; 438/248;	Birner; Albert et al.

		semiconductor device with trench capacitors		438/255; 438/387; 438/389; 438/392	
US 6867105 B2	20050315	Bipolar transistor and method of fabricating a bipolar transistor	438/320	257/197; 257/E21.379; 257/E29.184; 438/364; 438/365; 438/366	Stengl; Reinhard et al.
US 6863769 B2	20050308	Configuration and method for making contact with the back surface of a semiconductor substrate	156/345.11	156/345.1; 156/345.19; 257/181; 257/414; 257/703; 438/107; 438/421; 438/746	Birner; Albert et al.
US 6762455 B2	20040713	Semiconductor component for high reverse voltages in conjunction with a low on resistance and method for fabricating a semiconductor component	257/335	257/339; 257/341; 257/342; 257/E21.42; 257/E29.013; 257/E29.021; 257/E29.04; 257/E29.066; 257/E29.257; 257/E29.259	Oppermann; Klaus-Gunter et al.
US 6746880 B2	20040608	Method for making electrical contact with a rear side of a semiconductor substrate during its processing	438/10	257/466; 438/421	Birner; Albert et al.
US 6724058 B2	20040420	Method for producing a filled recess in a material layer, and an integrated circuit configuration produced by the method	257/415	257/301; 257/353; 257/417; 257/418; 257/419; 257/513; 438/50; 438/53	Aigner; Robert et al.
US 6635545	20031021	Method for	438/348	257/572;	Bock; Josef

B2		fabricating a bipolar transistor and method for fabricating an integrated circuit configuration having such a bipolar transistor		257/E21.371; 257/E21.379	et al.
US 6605487 B2	20030812	Method for the manufacture of micro-mechanical components	438/50		Franosch; Martin et al.
US 6556418 B2	20030429	Micromechanical component and process for its fabrication	361/283.1	257/417; 257/419; 361/280; 361/283.4; 438/52; 438/53	Aigner; Robert et al.
US 6552385 B2	20030422	DRAM memory capacitor having three-layer dielectric, and method for its production	257/310	257/296; 257/304; 257/306; 257/311; 257/E21.01; 257/E21.272	Beitel; Gerhard et al.
US 6548846 B2	20030415	Storage capacitor for a DRAM	257/296	257/E21.647; 257/E27.085; 438/240; 438/3; 438/397	Reisinger; Hans et al.
US 6406933 B1	20020618	Production method for micromechanical components	438/53		Aigner; Robert et al.
US 6401544 B2	20020611	Micromechanical component protected from environmental influences	73/754		Aigner; Robert et al.
US 6373115 B1	20020416	Micromechanical structure, sensor and method for manufacturing the same	257/414	257/415; 257/417; 257/418; 257/419; 257/467; 438/5; 438/51;	Kolb; Stefan et al.

				438/53; 438/7; 438/702; 438/756	
US 6346429 B1	20020212	Method for fabricating integrated sensors	438/48	257/414; 257/419; 257/E27.014; 438/51; 438/52; 438/53; 73/514.16	Aigner; Robert et al.
US 6215140 B1	20010410	Electrically programmable non-volatile memory cell configuration	257/296	257/298; 257/302; 257/314; 257/321; 257/328; 257/330; 257/E21.613; 257/E27.073; 438/156; 438/243; 438/253; 438/259; 438/300; 438/542; 438/644	Reisinger; Hans et al.
US 6204119 B1	20010320	Manufacturing method for a capacitor in an integrated memory circuit	438/254	257/E21.016; 438/396; 438/970	Lange; Gerrit et al.
US 6197666 B1	20010306	Method for the fabrication of a doped silicon layer	438/509	257/E21.197; 257/E21.297; 257/E21.585; 257/E21.654	Schafer; Herbert et al.
US 6194765 B1	20010227	Integrated electrical circuit having at least one memory cell and method for fabricating it	257/369	257/334; 257/368; 257/371; 257/372; 257/903; 257/E21.661; 257/E27.099	Reisinger; Hans et al.
US 6159815 A	20001212	Method of producing a MOS transistor	438/305	257/E21.431; 257/E21.64; 438/230; 438/306;	Lustig; Bernhard et al.

				438/307	
US 6140177 A	20001031	Process of forming a semiconductor capacitor including forming a hemispherical grain statistical mask with silicon and germanium	438/253	257/E21.014; 257/E21.02; 438/396; 438/398; 438/947	Schafer; Herbert et al.
US 6133126 A	20001017	Method for fabricating a dopant region	438/564	257/E21.15; 257/E21.592; 257/E21.645; 257/E27.081; 438/542	Reisinger; Hans et al.
US 6127220 A	20001003	Manufacturing method for a capacitor in an integrated storage circuit	438/254	257/E21.648; 257/E27.089; 438/396	Lange; Gerrit et al.
US 6117790 A	20000912	Method for fabricating a capacitor for a semiconductor memory configuration	438/712	257/E21.012; 257/E21.648; 257/E27.089; 438/719; 438/734; 438/754; 438/756	Schafer; Herbert et al.
US 6040995 A	20000321	Method of operating a storage cell arrangement	365/185.18	257/324; 257/E29.165; 257/E29.309; 365/185.01; 365/185.03; 365/185.14; 365/189.01	Reisinger; Hans et al.
US 6022786 A	20000208	Method for manufacturing a capacitor for a semiconductor arrangement	438/398	257/E21.651; 361/313; 438/397	Franosch; Martin et al.
US 5998807 A	19991207	Integrated CMOS circuit arrangement and method for the manufacture	257/66	257/347; 257/E21.699; 257/E27.062; 257/E27.112	Lustig; Bernhard et al.

		thereof			
US 5994751 A	19991130	Photodiode having reduced series resistance, and method for fabrication thereof	257/446	257/461; 257/466; 257/594; 257/E21.564; 257/E31.039; 257/E31.057	Oppermann; Klaus-Gunter
US 5943571 A	19990824	Method for manufacturing fine structures	438/257	117/102; 117/923; 117/925; 257/E21.036; 257/E21.131; 257/E21.422; 257/E21.68; 438/700; 438/706; 438/719	Schaefer; Herbert et al.
US 5817553 A	19981006	Process for manufacturing capacitors in a solid state configuration	438/253	257/E21.648; 257/E27.089; 438/254	Stengl; Reinhard et al.